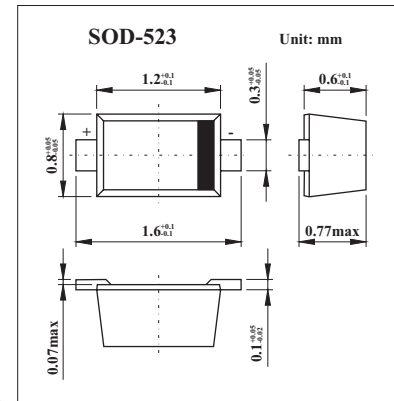


Schottky Barrier Diode

1PS79SB10

■ Features

- Low forward voltage
- Guard ring protected
- Ultra small plastic SMD package.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
continuous reverse voltage	V _R	30	V
continuous forward current	I _F	200	mA
repetitive peak forward current *	I _{FRM}	300	mA
non-repetitive peak forward current tp < 10 ms	I _{FSM}	600	mA
operating ambient temperature	T _{amb}	-65 to 125	°C
thermal resistance from junction to ambient	R _{thj-a}	450	K/W
junction temperature	T _j	125	°C
storage temperature	T _{stg}	-65 to 150	°C

* tp ≤ 1 s; d ≤ 0.5

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
continuous forward voltage	V _F	I _F = 0.1 mA			240	mV
		I _F = 1 mA			320	mV
		I _F = 10 mA			400	mV
		I _F = 30 mA			500	mV
		I _F = 100 mA			800	mV
continuous reverse current	I _R	V _R = 25 V *			2	μ A
diode capacitance	C _d	V _R = 1 V; f = 1 MHz			10	pF

* Pulsed test: tp = 300 μ s; δ = 0.02.

■ Marking

Marking	F
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